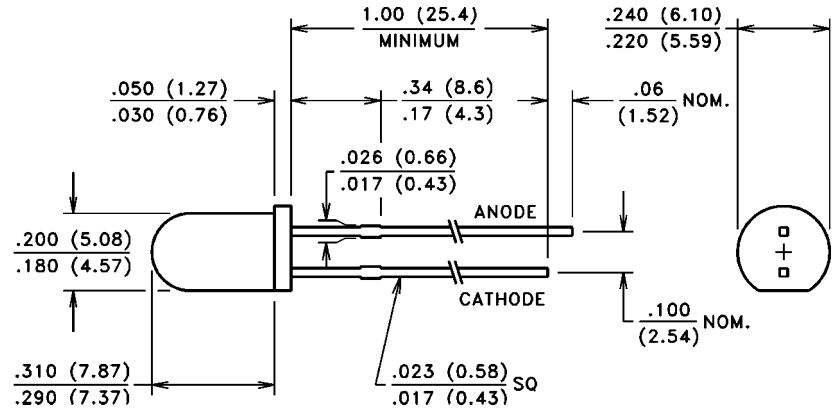




(Also available in infrared transmitting visible blocking version)

## PACKAGE DIMENSIONS inch (mm)



CASE 26 T-1 $\frac{3}{4}$

CHIP ACTIVE AREA: .0036 in<sup>2</sup> (2.326 mm<sup>2</sup>)

## PRODUCT DESCRIPTION

This photodiode features the largest detection area available in a clear, endlooking T-1 $\frac{3}{4}$  package. Combined with excellent dark current, it can fulfill the demands of many difficult applications.

## ABSOLUTE MAXIMUM RATINGS

Storage Temperature: -40°C to 100°C  
 Operating Temperature: -40°C to 100°C

RoHS Compliant



## ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also VTP curves, pages 45-46)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VTP1232H			UNITS
			Min.	Typ.	Max.	
I <sub>SC</sub>	Short Circuit Current	H = 100 fc, 2850 K	100			μA
TC I <sub>SC</sub>	I <sub>SC</sub> Temperature Coefficient	2850 K		0.20		%/°C
Re	Responsivity	880 nm	0.06	0.076		A/(W/cm <sup>2</sup> )
V <sub>OC</sub>	Open Circuit Voltage	H = 100 fc, 2850 K	.42			mV
TC V <sub>OC</sub>	V <sub>OC</sub> Temperature Coefficient	2850 K		-2.0		mV/°C
I <sub>D</sub>	Dark Current	H = 0, VR = 10 V			25	nA
C <sub>J</sub>	Junction Capacitance	H = 0, V = 0 V		.18	.30	nF
λ <sub>range</sub>	Spectral Application Range		400		1100	nm
λ <sub>p</sub>	Spectral Response - Peak			920		nm
S <sub>R</sub>	Sensitivity	@ Peak		0.60		A/W